

30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}=30V$; $R_{DS(ON)}=0.22\Omega$; $I_D=1.4A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

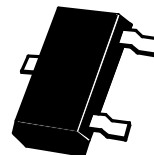
- DC - DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

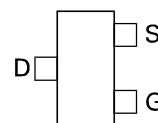
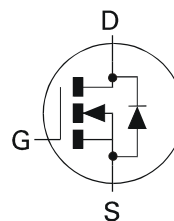
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXM61N03FTA	7	8mm embossed	3000 units
ZXM61N03FTC	13	8mm embossed	10000 units

DEVICE MARKING

- N03



SOT23



Top View

ZXM61N03F

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS}=10V$; $T_A=25^\circ C$)(b) ($V_{GS}=10V$; $T_A=70^\circ C$)(b)	I_D	1.4 1.1	A
Pulsed Drain Current (c)	I_{DM}	7.3	A
Continuous Source Current (Body Diode) (b)	I_S	0.8	A
Pulsed Source Current (Body Diode)	I_{SM}	7.3	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^\circ C/W$

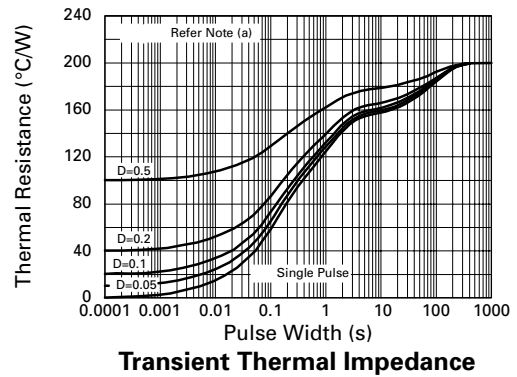
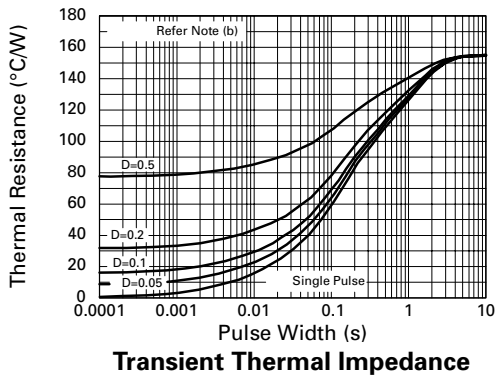
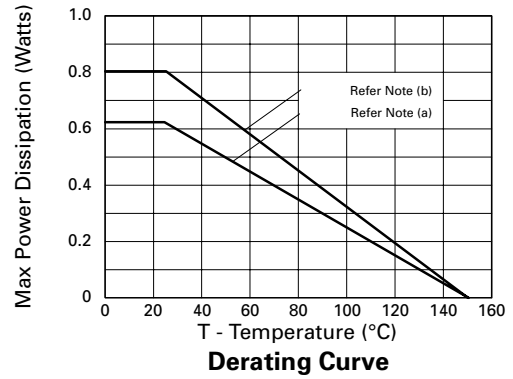
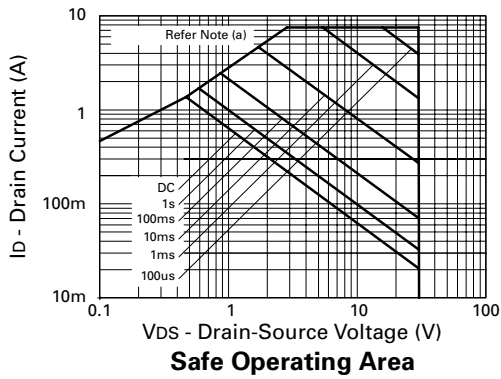
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

CHARACTERISTICS



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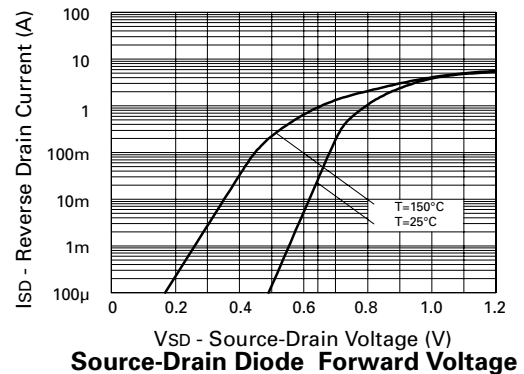
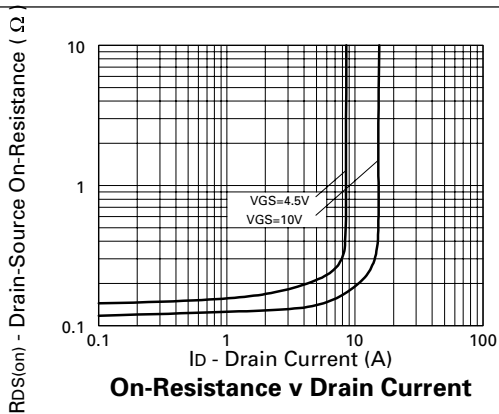
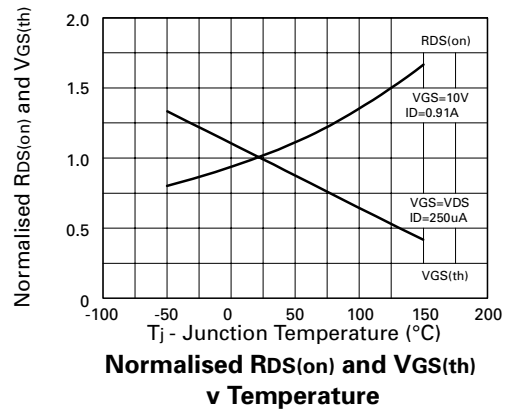
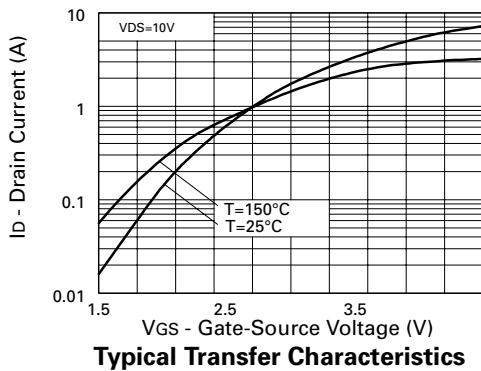
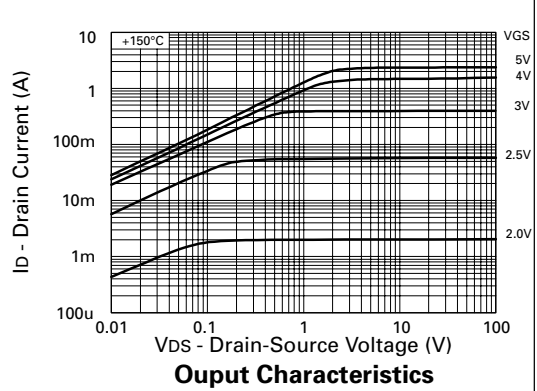
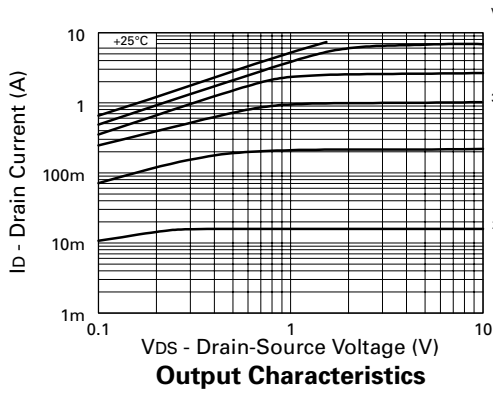
ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.(3)	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =± 20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.22 0.30	Ω Ω	V _{GS} =10V, I _D =0.91A V _{GS} =4.5V, I _D =0.46A
Forward Transconductance (3)	g _{fs}	0.87			S	V _{DS} =10V, I _D =0.46A
DYNAMIC (3)						
Input Capacitance	C _{iss}		150		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{Oss}		35		pF	
Reverse Transfer Capacitance	C _{rss}		15		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.9		ns	V _{DD} =15V, I _D =0.91A R _G =6.2Ω, R _D =16Ω (refer to test circuit)
Rise Time	t _r		2.5		ns	
Turn-Off Delay Time	t _{d(off)}		5.8		ns	
Fall Time	t _f		3.0		ns	
Total Gate Charge	Q _g			4.1	nC	V _{DS} =24V, V _{GS} =10V, I _D =0.91A (refer to test circuit)
Gate-Source Charge	Q _{gs}			0.4	nC	
Gate-Drain Charge	Q _{gd}			0.63	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _J =25°C, I _S =0.91A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		11.0		ns	T _J =25°C, I _F =0.91A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		3.5		nC	

NOTES

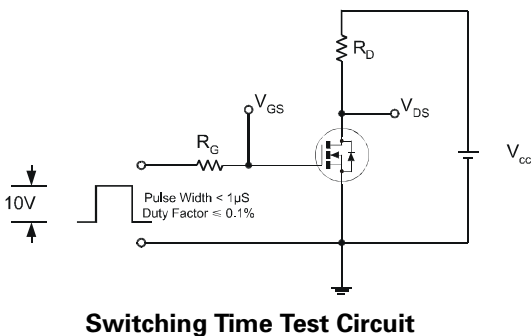
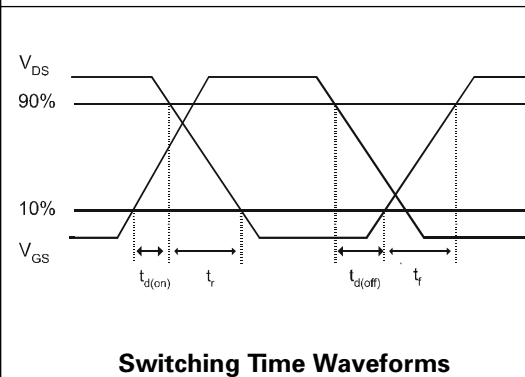
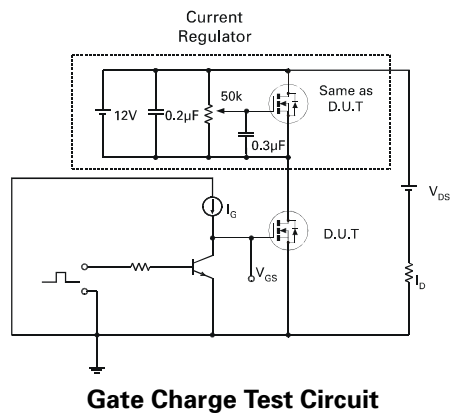
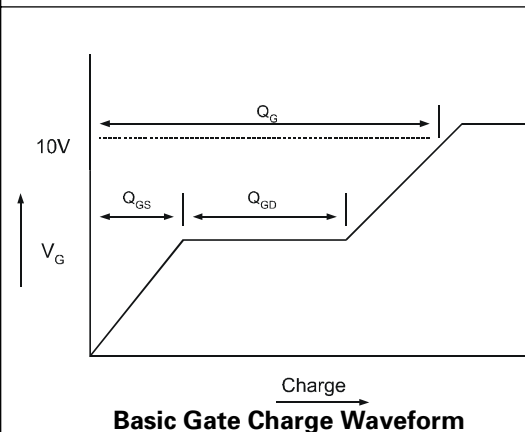
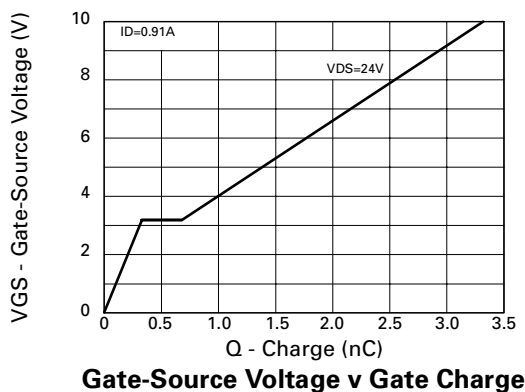
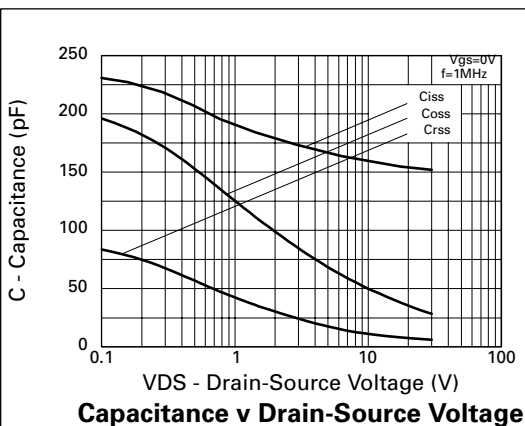
- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

TYPICAL CHARACTERISTICS



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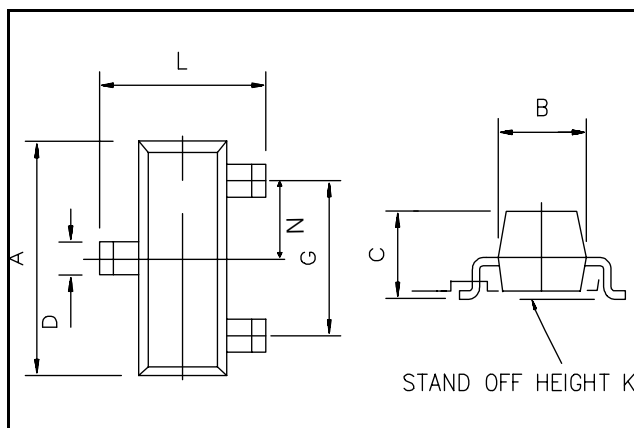
TYPICAL CHARACTERISTICS



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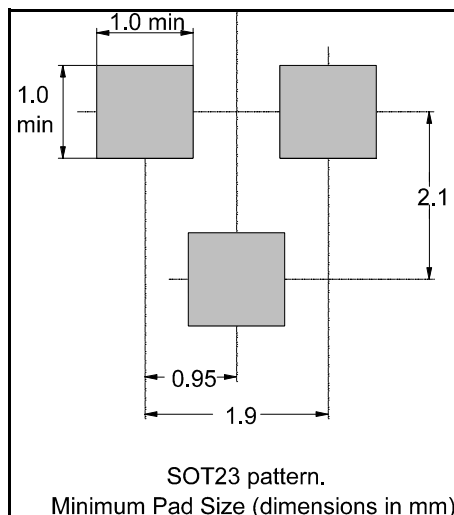
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PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	2.67	3.05	0.105	0.120
B	1.20	1.40	0.047	0.055
C	—	1.10	—	0.043
D	0.37	0.53	0.0145	0.021
F	0.085	0.15	0.0033	0.0059
G	NOM 1.9		NOM 0.075	
K	0.01	0.10	0.0004	0.004
L	2.10	2.50	0.0825	0.0985
N	NOM 0.95		NOM 0.037	

PAD LAYOUT DETAILS



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